## SC12804TP

PTO/SB/08A (04-03)

Substitute for form 1449A/PTO Complete if Known 10/650,002 **Application Number** 8/27/2003 Filing Date Concurrently Herewith INFORMATION DISCLOSURE Varughese Mathew et al. First Named Inventor STATEMENT BY APPLICANT Group Art Unit 2825 Everhand **Examiner Name** (use as many sheets as necessary) Attorney Docket Number SC12804TP of Sheet **U. S. PATENT DOCUMENTS** Name of Patentee or Applicant Pages, Columns, Lines, Where Relevant **Publication Date** Examiner Cite No. 1 **Document Number** Passages or Relevant Figures Appear of Cited Document MM-DD-YYYY Initials\* Number -Kind Code<sup>2</sup> (if known) 12/09/1997 Dubin et al. 1 me AA 5,695,810 06/19/2003 Chebiam et al. cone AB 2003/0113576 A1

FOREIGN PATENT DOCUMENTS						
Examine r Initials*	Cite No. 1	Foreign Patent Document Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T 6
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	NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No. 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T2			
CYME	AC	Itabashi et al., "Electroless Deposited CoWB for Copper Diffusion Barrier Metal," Proceedings of the IEEE 2002 International Interconnect Technology Conference (Cat. No. 02EX519), 2002, pp. 285-287.				

Examiner Signature	C. Everhand	Date Considered	10-29-04
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1449A/PTO

Sheet

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## **INFORMATION DISCLOSURE**

of

STATEMENT BY APPLICANT (use as many sheets as necessary)

Complete if Known					
Application Number	10/650,002				
Filing Date	August 27, 2003				
First Named Inventor	Varughese Mathew et al.				
Group Art Unit	1762 2825T				
Examiner Name	Unassigned C. Everhart				
Attorney Docket Number	SC12804TP				

U. S. PATENT DOCUMENTS							
Examiner Initials*  Cite No. 1 Document Number Publication Date Name of Patentee or Applicant Pages, Columns, Lines, Where Relevant Possages or Relevant Figures Appear							
OME	BA	6,528,409 B1	03/04/2003	Lopatin et al.			
cyne	BB	2003/0111729 A1	06/19/2003	Leu et al.			

FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. 1	Foreign Patent Document Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	Т 6		

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Examiner Initials*	Cite No. 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	İs
CME	BC	Duch et al., "Development and Characterization of Co-Ni Alloys for Microsystems Applications," Journal of the Electrochemical Society, 2002, 149(4), pp. C201-C208.	
CAME	BD	Homma et al., "Microstructural Study of Electroless-Plated CoNiP Ternary Alloy Films for Perpendicular Magnetic Recording Media," <i>IEEE Transactions on Magnetics</i> , November 1991, 27(6), pp. 4909-4911.	
CYME	BE	Kohn et al., "Characterization of Electroless Deposited Co(W,P) Thin Films for Encapsulation of Copper Metallization," Materials Science and Engineering, 2001, A302, pp. 18-25.	
CYME	BF	Kohn et al., "Evaluation of Electroless Deposited Co(W,P) Thin Films as Diffusion Barriers for Copper Metallization," Microelectronic Engineering, 2001, 55, pp. 297-303.	
ame	BG	Petrov et al., "Electrochemical Study of the Electroless Deposition of Co(P) and Co (W,P) Alloys," Journal of the Electrochemical Society, 2002, 149(4), C187-C194.	
CYME	ВН	Osaka et al., "Fabrication of Electroless NiReP Barrier Layer on SiO₂ without Sputtered Seed Layer," Electrochemical and Solid-State Letters, 2002, 5(1), pp. C7-C10.	
CYME	ВІ	O'Sullivan et al., "Electrolessly Deposited Diffusion Barriers for Microelectronics," IBM Journal of Research and Development, September 1998, Vol. 42, No. 5, pp. 607-620.	
COME	ม	Segawa et al., "Manufacturing-ready Selectivity of CoWP Capping on Damascene Copper Interconnects," Advanced Metallization Conference 2001, AMC 2001 Proceedings of the Conference, pp. 567-572.	
COME	BK	Shacham-Diamand et al., "Electroless Co(W,P) and Co (Mo,P) Deposition for Cu Metallization Applications," IEEE, 2001 6th International Conference on Solid State and Integrated Circuit Technology, Vol. 1, 2001, pp. 410-415.	
CME	BL	Shacham-Diamand et al., "Electroless Deposition of Thin-Film Cobalt-Tungsten-Phosphorus Layers Using Tungsten Phosphoric Acid (H <sub>3</sub> [P(W <sub>3</sub> O <sub>10</sub> ) <sub>4</sub> ]) for ULSI and MEMS Application," Journal of the Electrochemical Society, 2001, 148(3), pp. C162-C167.	
CAME	ВМ	Shacham-Diamand et al., "Material Properties of Electroless 100-200 nm Thick CoWP Films,"  Electrochemical Technology Applications in Electronics Proceedings of the Third International Symposium Electrochemical Society Proceedings, 2000, Vol. 99-34, pp. 102-110.	

Examiner Signature	O. Luerhast	Date	10-29-04
EVALUED 1 is 10		Considered	

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